

IDS-1-20-2004

Sheet 1 of 6



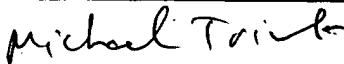
10/762,097

<b>FORM PTO-1449 (SUBSTITUTE)</b>  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  <b>INFORMATION DISCLOSURE          STATEMENT BY APPLICANT</b> (37 CFR 1.98(b))				Attorney Docket No.: P2001,0520 Appl. No.: <u>10/762,097</u>  Applicant: BERTHOLD HAHN ET AL.  Filing Date: January 20, 2004 Group Art Unit: <u>2822</u>			
EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE	
MT	A	6,015,979	1/18/00	Sugiura et al.	—		
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<b>FOREIGN PATENT DOCUMENT</b>							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
MT	J	0 732 754 A2	9/18/96	Europe	—		
MT	K	0 599 224 B1 and A1	6/1/94	Europe	—		
MT	L	0 993 048 A2	4/12/00	Europe	—		
	M						
	N						
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
MT		Kim, I.-H. et al.: "Formation of V-Shaped Pits in InGaN/GaN Multiquantum Wells and Bulk InGaN Films", Applied Physics Letters, Vol. 73, No. 12, September 21, 1998, pp. 1634-1636					
MT		Chen, Y. et al.: "Pit Formation in GaInN Quantum Wells", Applied Physics Letters, Vol. 72, No. 6, February 9, 1998, pp. 710-712					
EXAMINER <u>Michael Trish</u>				DATE CONSIDERED <u>10/30/05</u>			



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MT		Wu, X. H. et al.: "Dislocation Generation in GaN Heteroepitaxy", Journal of Crystal Growth, Elsevier Science B.V., 189/190, 1998, pp. 231-243					
MT		Kawaguchi, Y. et al.: "The Formation of Crystalline Defects and Crystal Growth Mechanism in In <sub>x</sub> Ga <sub>1-x</sub> N/GaN Heterostructure Grown by Metalorganic Vapor Phase Epitaxy", Journal of Crystal Growth, Elsevier Science B.V., 189/190, 1998, pp. 24-28					
EXAMINER <i>Michael T. ...</i>				DATE CONSIDERED <i>10/30/05</i>			


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MT		Gallart, M. et al.: "CW and Time-Resolved Optical Spectroscopy of GaN Epilayers and GaN-AlGaIn Quantum Wells Grown on A-Plane Sapphire", Phys.Stat.Sol., (b), 216, 365, 1999, pp. 365-369					
MT		Keller, S. et al.: "Spiral Growth of InGaIn Nanoscale Islands on GaN", Japanese Journal of Applied Physics, Vol. 37, Part 2, No. 4B, April 15, 1998, pp. L431-L434					
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
		Hangleiter, A. et al.: "Optical Absorption and Excitation Spectroscopy on GaInN/GaN Double Heterostructures and Quantum Wells", Materials Science Forum, Trans Tech Publications, Switzerland, Vols. 267-268, 1998, pp. 1287-1290					
		Im, J. S. et al.: "Reduction of Oscillator Strength due to Piezoelectric Fields in GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N Quantum Wells", The American Physical Society, Physical Review B, Vol. 57, No. 16, April 15, 1998, pp. R9435-R9438					
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		Nakamura, S. et al.: "High-Power InGaN Single-Quantum-Well-Structure Blue and Violet Light-Emitting Diodes", American Institute of Physics, Appl. Phys. Lett. 67, (13), September 25, 1995, pp. 1868-1870					
		Mukai, T.: "InGaN-Based Blue Light-Emitting Diodes Grown on Epitaxially Laterally Overgrown GaN Substrates", Publication Board, Japanese Journal of Applied Physics, Vol. 37, Part 2, No. 7B, July 15, 1998, pp. L839-L841					
EXAMINER <i>Michael Trinh</i>				DATE CONSIDERED <i>10/30/05</i>			

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		Lester, S. D. et al.: "High Dislocation Densities in High Efficiency GaN-Based Light-Emitting Diodes", American Institute of Physics, Appl. Phys. Lett., Vol. 66, No. 10, March 6, 1995, pp. 1249-1251					
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